

DERWENT-ACC-NO: 2003-575775

DERWENT-WEEK: 200354

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TITLE: Dry development having bilayer
resist - with a better
process window

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PRIORITY-DATA: 2001TW-0120355 (August 20, 2001)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	MAIN-IPC
TW 511151 A		November 21, 2002	N/A
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APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
TW 511151A	N/A	
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INT-CL (IPC): H01L021/027

ABSTRACTED-PUB-NO: TW 511151A

BASIC-ABSTRACT:

NOVELTY - The present invention discloses a dry development having bilayer resist. Firstly, an insulating layer, a first resist layer and a second resist layer are formed sequentially on a semiconductor substrate. Then, the second resist pattern is transferred accurately to the first resist layer using oxygen, nitrogen and argon gases as the reaction gas of dry development and the

surface of insulating layer is exposed after defining the
second resist pattern
using the conventional microlithography process.

CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS: DRY DEVELOP RESIST PROCESS WINDOW

DERWENT-CLASS: U11

EPI-CODES: U11-C04D; U11-C04E1;

SECONDARY-ACC-NO:

Non-CPI Secondary Accession Numbers: N2003-457636